

High Voltage Transistors

FEATURE

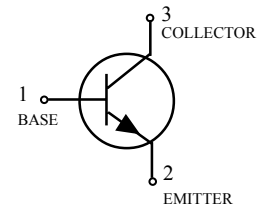
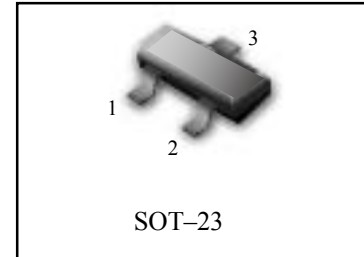
- Pb-Free package is available.

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
2N5550S	F0	3000/Tape&Reel
2N5551S	F1	3000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	140	Vdc
Collector–Base Voltage	V_{CBO}	160	Vdc
Emitter–Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	600	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage(3) ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$			Vdc
2N5550S		140	–	
2N5551S		160	–	
Collector–Base Breakdown Voltage ($I_C = 100 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$			Vdc
2N5550S		160	–	
2N5551S		160	–	
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$			Vdc
		6.0	–	
Collector Cutoff Current ($V_{CB} = 100 \text{ Vdc}, I_E = 0$)	I_{CBO}			nAdc
2N5550S		–	100	
2N5551S		–	50	
($V_{CB} = 100 \text{ Vdc}, I_E = 0, T_A = 100^\circ\text{C}$)				μAdc
2N5550S		–	100	
2N5551S		–	50	
Emitter Cutoff Current ($V_{BE} = 4.0 \text{ Vdc}, I_C = 0$)	I_{EBO}			nAdc
		–	50	

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.
- Pulse Test: Pulse Width = $300 \mu\text{s}$, Duty Cycle = 2.0%.



2N5550S 2N5551S

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

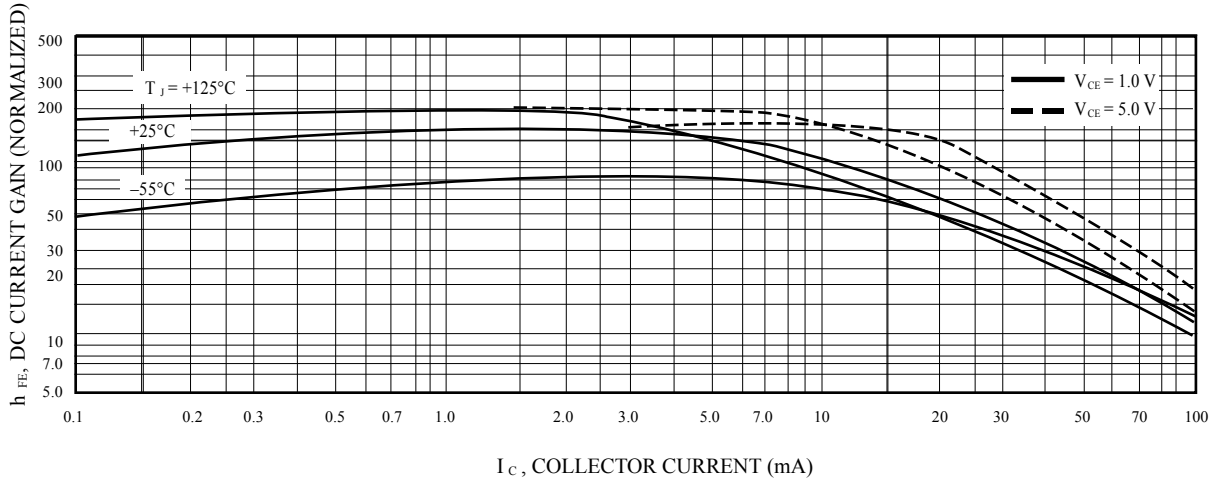
Characteristic	Symbol	Min	Max	Unit
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ON CHARACTERISTICS

DC Current Gain (I _C = 1.0 mA _{dc} , V _{CE} = 5.0 V _{dc})	2N5550S	h _{FE}	60	—	—
	2N5551S		80	—	
(I _C = 10 mA _{dc} , V _{CE} = 5.0 V _{dc})	2N5550S		60	250	
	2N5551S		80	250	
(I _C = 50 mA _{dc} , V _{CE} = 5.0V _{dc})	2N5550S		20	—	
	2N5551S		30	—	
Collector–Emitter Saturation Voltage (I _C = 10 mA _{dc} , I _B = 1.0 mA _{dc})	Both Types	V _{CE(sat)}	—	0.15	V _{dc}
(I _C = 50 mA _{dc} , I _B = 5.0 mA _{dc})	2N5550S		—	0.25	
	2N5551S		—	0.20	
Base–Emitter Saturation Voltage (I _C = 10 mA _{dc} , I _B = 1.0 mA _{dc})	Both Types	V _{BE(sat)}	—	1.0	V _{dc}
(I _C = 50 mA _{dc} , I _B = 5.0 mA _{dc})	2N5550S		—	1.2	
	2N5551S		—	1.0	

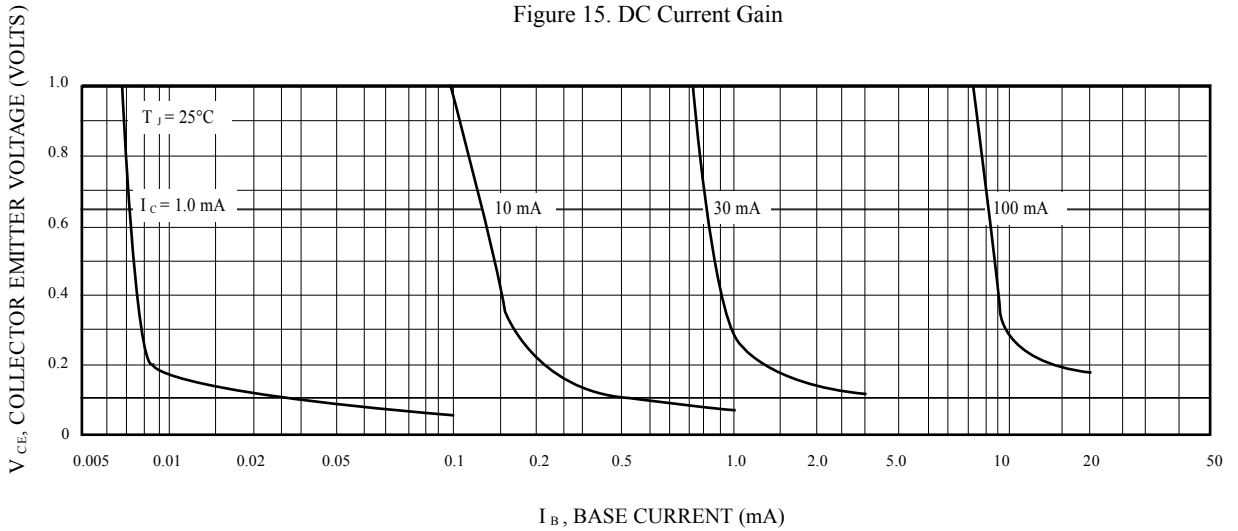


2N5550S 2N5551S



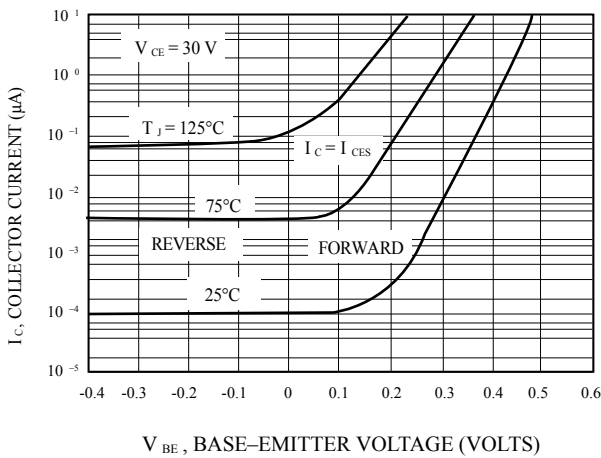
I_C , COLLECTOR CURRENT (mA)

Figure 15. DC Current Gain



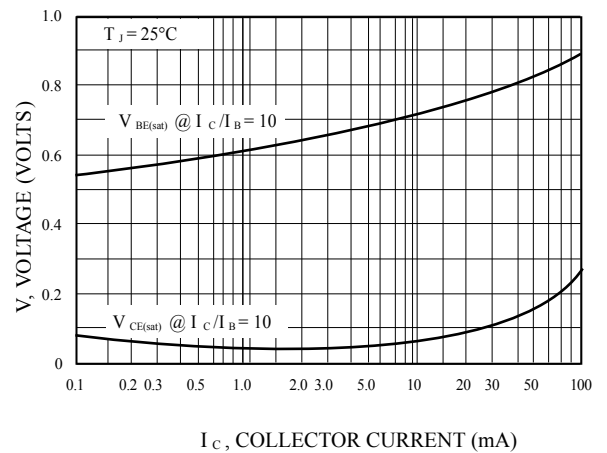
I_B , BASE CURRENT (mA)

Figure 16. Collector Saturation Region



V_{BE} , BASE-EMITTER VOLTAGE (VOLTS)

Figure 3. Collector Cut-Off Region



I_C , COLLECTOR CURRENT (mA)

Figure 4. "On" Voltages

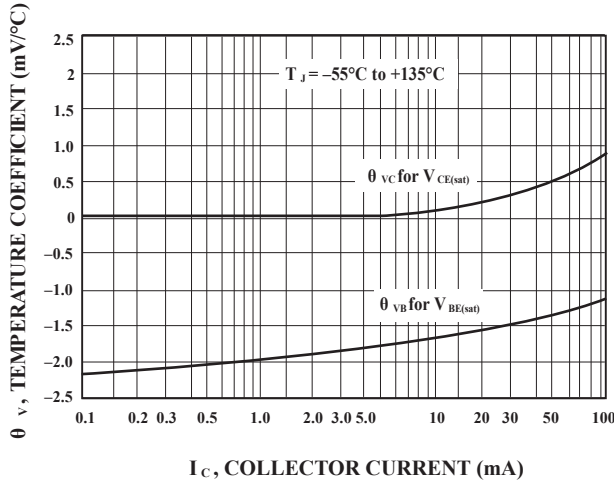
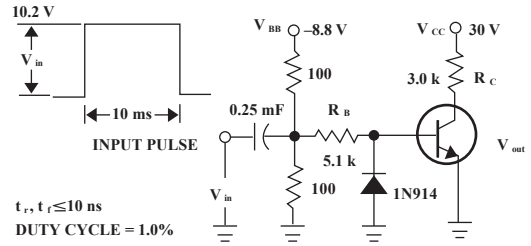


Figure 5. Temperature Coefficients



Values Shown are for $I_C @ 10 \text{ mA}$
Figure 6. Switching Time Test Circuit

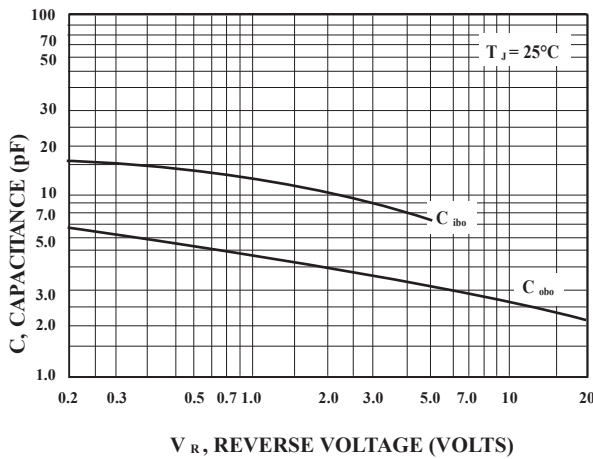
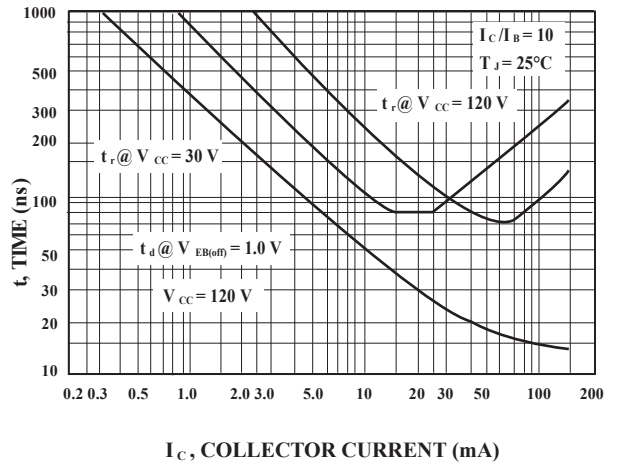


Figure 7. Capacitances Figure



8. Turn-On Time

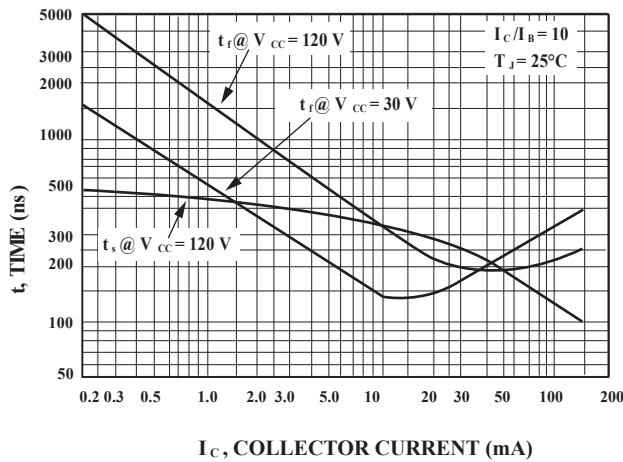
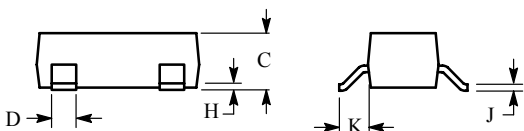
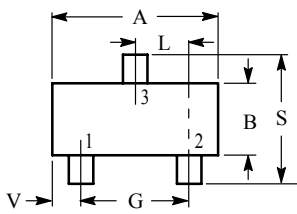


Figure 9. Turn-Off Time

SOT-23



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

